LDMOS 2-stage integrated Doherty MMIC

Rev. 1 — 11 November 2022

1. Product profile

1.1 General description

The B10G2327N55D is a 2-stage fully integrated asymmetrical Doherty MMIC solution using Ampleon's state of the art LDMOS technology. The carrier and peaking device, input splitter, output combiner and pre-match are integrated in a single package. This device is perfectly suited as general purpose driver or mMIMO final in the frequency range from 2300 MHz to 2700 MHz. Available in PQFN outline.

Table 1. Application performance

Typical RF performance at $T_{case} = 25 \ ^{\circ}C$; $I_{Dq} = 49 \ mA$ (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.31 \ V$. Test signal: 1-carrier LTE 20 MHz; PAR = 7.6 dB at 0.01 % probability CCDF measured in an Ampleon $f = 2600 \ MHz$ integrated Doherty application circuit.

Test signal	f	V _{DS}	P _{L(AV)}	G _p	ησ
	(MHz)	(V)	(W)	(dB)	(%)
1-carrier LTE 20 MHz PAR = 7.6 dB	2600	28	2.51	29.9	35.6

1.2 Features and benefits

- Integrated input splitter
- Integrated output combiner
- Source impedance 50 Ω
- Pre-matched output
- High efficiency by asymmetric Doherty design
- Designed for large RF and instantaneous bandwidth operation, covering frequency from 2300 MHz to 2700 MHz
- Independent control of carrier and peaking bias
- Integrated ESD protection
- High power gain
- For RoHS compliance see the product details on the Ampleon website

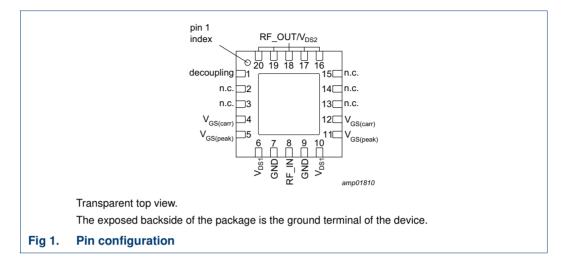
1.3 Applications

RF power MMIC for multi-carrier and multi-standard GSM, W-CDMA and LTE base stations in the 2300 MHz to 2700 MHz frequency range

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2. Pinning information

2.1 Pinning



2.2 Pin description

Table 2. Pin description

Symbol	Pin	Description				
decoupling	1	video-lead for decoupling				
n.c.	2	not connected				
n.c.	3	not connected				
V _{GS(carr)}	4	gate-source voltage of carrier [1]				
V _{GS(peak)}	5	gate-source voltage of peaking [2]				
V _{DS1}	6	drain-source voltage of driver stages 3				
GND	7	RF ground				
RF_IN	8	RF input				
GND	9	RF ground				
V _{DS1}	10	drain-source voltage of driver stages 3				
V _{GS(peak)}	11	gate-source voltage of peaking [2]				
V _{GS(carr)}	12	gate-source voltage of carrier [1]				
n.c.	13, 14, 15	not connected				
RF_OUT/V _{DS2}	16	RF output / drain-source voltage of final stages				
RF_OUT/V _{DS2}	17	RF output / drain-source voltage of final stages				
RF_OUT/V _{DS2}	18	RF output / drain-source voltage of final stages				
RF_OUT/V _{DS2}	19	RF output / drain-source voltage of final stages				
RF_OUT/V _{DS2}	20	RF output / drain-source voltage of final stages				
GND	flange	RF ground				

[1] Pins connected together.

[2] Pins connected together.

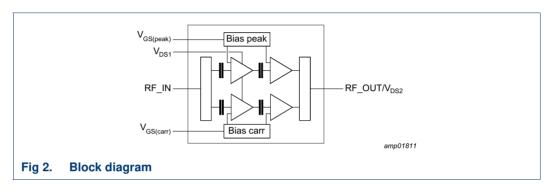
 $[3] \quad I_{max(DC)} \leq 300 \text{ mA}.$

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3. Ordering information

Table 3. Ordering information								
Package name	Orderable part number	12NC		Min. orderable quantity (pieces)				
SOT1462-1	B10G2327N55DZ	9349 605 86515	TR13; 500-fold; 16 mm; dry pack	500				

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage		-0.5	+65	V
V _{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	200	°C

[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

6. Thermal characteristics

Table 5. Thermal characteristics

 $V_{DS} = 28 V$; $I_{Dq} = 49 mA$ (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} = -0.31 V$.

Symbol	Parameter	Conditions		Value	Unit
R _{th(j-c)}	thermal resistance from junction to case	$T_{case} = 90 \ ^{\circ}C; P_{L} = 2.51 \ W$	[1]	4.5	K/W
		$T_{case} = 90 \ ^{\circ}C; P_{L} = 7.94 \ W$	[1]	3.1	K/W
		$T_{case} = 90 \ ^{\circ}C; P_{L} = 10 \ W$	[1]	2.8	K/W

[1] When operated with a 1-carrier W-CDMA with PAR = 9.9 dB.

Unit

٧ nΑ

nA

μA

μA

1.4

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Characteristics 7.

Table 6 DC characteristics

Symbol	Parameter	Conditions	Min	Тур	Ма
Carrier					_
V _{GSq}	gate-source quiescent voltage	$V_{DS} = 28 \text{ V}; I_D = 42 \text{ mA}$	1.8	2.2	2.5
I _{GSS}	gate leakage current	$V_{GS} = 9 V; V_{DS} = 0 V$	-	-	32
Peaking					_
I _{GSS}	gate leakage current	$V_{GS} = 9 V; V_{DS} = 0 V$	-	-	32
Final sta	ges				
I _{DSS}	drain leakage current	$V_{GS} = 0 V; V_{DS} = 28 V$	-	-	1.4
Driver st	ades	-			

Table 7. **RF** characteristics

IDSS

drain leakage current

Typical RF performance at $T_{case} = 25 \ ^{\circ}C$; $V_{DS} = 28 \ V$; $I_{Dq} = 42 \ mA$ (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.4 \ V$; $P_{L(AV)} = 8 \ W$; $f = 2500 \ MHz$ measured in an Ampleon production circuït.

 $V_{GS} = 0 V; V_{DS} = 28 V$

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
Test signal: pulsed CW [1]								
G _p	power gain		24.8	27.5	31.2	dB		
η _D	drain efficiency	P _L = 8 W (39 dBm)	35	43	-	%		
		$P_L = P_{L(3dB)}$	42	48	-	%		
RL _{in}	input return loss		-	-	-10	dB		
P _{L(3dB)}	output power at 3 dB gain compression		45.9	46.8	-	dBm		

[1] Pulsed CW power sweep measurement (δ = 10 %, t_p = 100 µs).

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8. Application information

8.1 Typical performance as driver application

Table 8. Typical performance

 $T_{case} = 25 \ ^{\circ}C; V_{DS} = 28 \ V; I_{Dq} = 49 \ mA \ (carrier); V_{GSq(peaking)} = V_{GSq(carrier)} - 0.31 \ V.$ Test signal: 1-carrier W-CDMA; PAR = 9.9 dB measured in an Ampleon 2500 MHz to 2700 MHz frequency band application circuit.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
P _{L(1dB)}	output power at 1 dB gain compression	f = 2600 MHz	[1]	-	46.4	-	dBm
P _{L(3dB)}	output power at 3 dB gain compression	f = 2600 MHz	f = 2600 MHz [1] -		47.3	-	dBm
$\phi_{s21}/\phi_{s21}(norm)$	normalized phase response	at 1 dB compression point; f = 2600 MHz	[2]	-	-8.9	-	0
η _D	drain efficiency	13.5 dB OBO (P _{L(AV)} = 34 dBm); f = 2600 MHz		-	35.7	-	%
G _p	power gain	$P_{L(AV)} = 34 \text{ dBm}; f = 2600 \text{ MHz}$		-	30	-	dB
B _{video}	video bandwidth	P _{L(AV)} = 34 dBm; f = 2600 MHz	[3]	-	>400	-	MHz
G _{flat}	gain flatness	P _{L(AV)} = 34 dBm; f = 2500 MHz to 2700 MHz		-	0.3	-	dB
ACPR _{5M}	adjacent channel power ratio (5M)	P _{L(AV)} = 34 dBm; f = 2600 MHz		-	-38.5	-	dBc
$\Delta G / \Delta T$	gain variation with temperature	f = 2600 MHz	[4]	-	0.05	-	dB/°C
К	Rollett stability factor	$T_{case} = -40 \text{ °C to } +125 \text{ °C}; f = 0.2 \text{ GHz}$ to 6 GHz	[4]	-	>1	-	

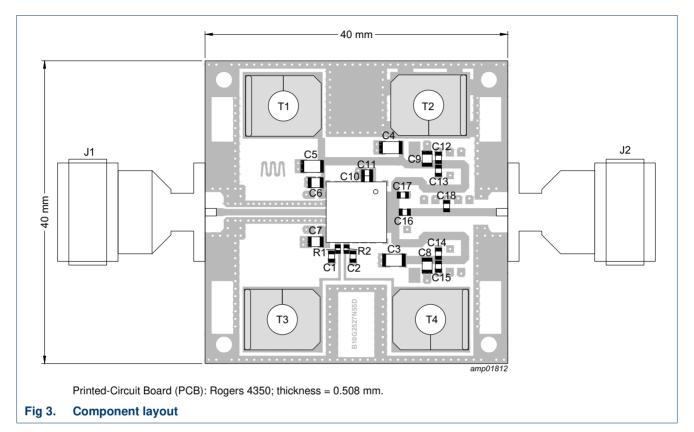
[1] Pulsed CW power sweep measurement (δ = 10 %; t_p = 100 µs).

[2] 25 ms CW power sweep measurement.

[3] Set to obtain IMD3 = -32 dBc.

[4] S-parameters measured with broadband demo board.

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8.2 PCB layout and electrical schematic

 Table 9.
 Demo test circuit list of components

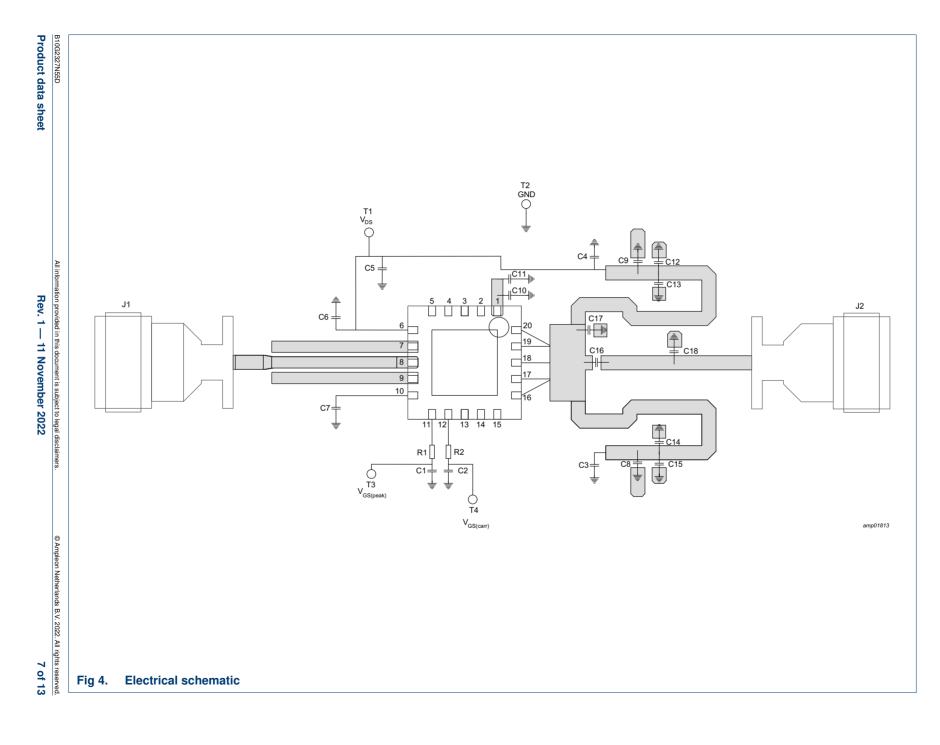
See Figure 3 for component layout.

Component	Description	Value	Remarks
C1, C2	multilayer ceramic chip capacitor	4.7 μF, 6.3 V	Murata: GRM155R60J475ME47D
C3, C4, C5	multilayer ceramic chip capacitor	10 μF, 50 V	Murata: GRM21BR6YA106KE43
C6,C7,C8,C9	multilayer ceramic chip capacitor	1 μF, 50 V	Murata: C1608X5R1H105K080AB
C10, C11, C12, C13, C14, C15	multilayer ceramic chip capacitor	100 nF, 50 V	Murata: 06035C104KAT2A
C16	multilayer ceramic chip capacitor	6.8 pF, ± 0.1 %	Murata: GQM1875C2E6R8BB12
C17	multilayer ceramic chip capacitor	0.5 pF, ± 0.1 %	Murata: GQM1875C2E0R5BB12
C18	multilayer ceramic chip capacitor	0.9 pF, ± 0.1 %	Murata: GQM1875C2E0R9BB12
R1, R2	resistor	1 k Ω , ± 1 %, 100 mW	Multicomp Pro: MCSR06X1001FTL
J1	N Coaxial panel connector male		Radiall: R161.438.200
J2	N Coaxial panel connector female		Huber & Suhner: 23_N-50-0-16/133_NE
T1, T2, T3, T4	PCB terminal	6.35 mm x 0.81 mm, 4.1 mm	TE connectivity: 141879-1

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B10G2327N55D





8.3 Ruggedness in a Doherty operation

8.3.1 Output mismatch ruggedness

The B10G2327N55D is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 32 V; I_{Dq} = 49 mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.31$ V; P_i corresponding to $P_{L(3dB)} - 9$ dB under Z_S = 50 Ω load; f = 2700 MHz (1-carrier W-CDMA; PAR = 9.9 dB); T_{case} = 25 °C.

8.3.2 Wideband noise ruggedness

The B10G2327N55D is capable of withstanding an AWGN (Additive White Gaussian Noise) with 11.2 dB PAR, OBW (Occupied BandWidth) of 800 MHz, under the following conditions: $V_{DS} = 32$ V; $I_{Dq} = 49$ mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.31$ V; 3 dB P_i overdrive from $P_{L(AV)} = 34$ dBm; f = 2600 MHz as central frequency; $T_{case} = 25$ °C.

8.4 Impedance information

Table 10. Typical impedance for optimum Doherty operation for 2.3 GHz to 2.4 GHz band Measured load-pull data; test signal: pulsed CW; $T_{case} = 25 \ ^{\circ}C$; $V_{DS} = 28 \ V$; $I_{Dq} = 48 \ mA$ (carrier); $V_{GSa(peaking)} = V_{GSa(carrier)} - 0.25 \ V$; $t_p = 100 \ \mu s$; $\delta = 10 \ ^{\circ}$.

	tuned for optimu	tuned for optimum Doherty operation						
f	Z _L [1]	P _{L(1dB)}	G _{p(max)}	໗ _{add} [2]	໗ _{add} [3]			
(MHz)	(Ω)	(dBm)	(dB)	(%)	(%)			
2200	11.6 – j10.9	45.9	30.17	45.15	30.45			
2300	14.0 – j9.5	46.0	30.39	47.35	32.40			
2400	17.0 – j11.5	46.1	30.50	49.50	32.50			

- [1] Reference package plane.
- [2] At P_{L(1dB)}.
- [3] At 34 dBm.

Table 11. Typical impedance for optimum Doherty operation for 2.5 GHz to 2.7 GHz band Measured load-pull data; test signal: pulsed CW; $T_{case} = 25 \ ^{\circ}C$; $V_{DS} = 28 \ V$; $I_{Dq} = 49 \ mA$ (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.31 \ V$; $t_p = 100 \ \mu s$; $\delta = 10 \ ^{\circ}$.

	tuned for optimu	tuned for optimum Doherty operation						
f	ZL ^[1]	P _{L(1dB)}	G _{p(max)}	໗ _{add} [2]	໗ _{add} [3]			
(MHz)	(Ω)	(dBm)	(dB)	(%)	(%)			
2500	16.9 – j11.6	46.2	30.1	53.8	36.8			
2600	16.4 – j7.9	46.4	30.2	56.0	37.6			
2700	15.5 – j4.9	46.3	30.4	57.3	36.7			
2800	14.4 – j4.5	46.0	29.9	57.2	35.8			

- [1] Reference package plane.
- [2] At P_{L(1dB)}.
- [3] At 34 dBm.

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9. Package outline

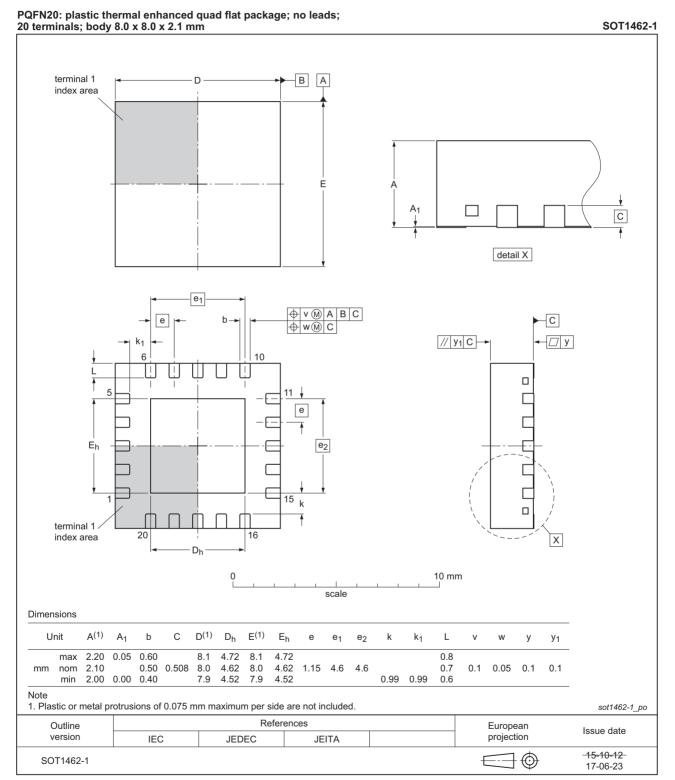


Fig 5. Package outline SOT1462-1 (PQFN20)

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10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 12.ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2B 🛄
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	1C 🛛

[1] CDM classification C2B is granted to any part that passes after exposure to an ESD pulse of 750 V.

[2] HBM classification 1C is granted to any part that passes after exposure to an ESD pulse of 1000 V.

11. Abbreviations

Table 13. Abbreviations				
Acronym	Description			
CCDF	Complementary Cumulative Distribution Function			
CW	Continuous Wave			
ESD	ElectroStatic Discharge			
GSM	Global System for Mobile Communications			
LDMOS	Laterally Diffused Metal Oxide Semiconductor			
LTE	Long Term Evolution			
MMIC	Monolithic Microwave Integrated Circuit			
mMIMO	massive Multiple Input Multiple Output			
MTF	Median Time to Failure			
OBO	Output Back Off			
PAR	Peak-to-Average Ratio			
RoHS	Restriction of Hazardous Substances			
VSWR	Voltage Standing Wave Ratio			
W-CDMA	Wideband Code Division Multiple Access			

12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
B10G2327N55D v.1	20221011	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 11 November 2022 Document identifier: B10G2327N55D